

Inchange Semiconductor

Product Specification

Silicon PNP Power Transistors

BD676A/678A/680A/682

DESCRIPTION

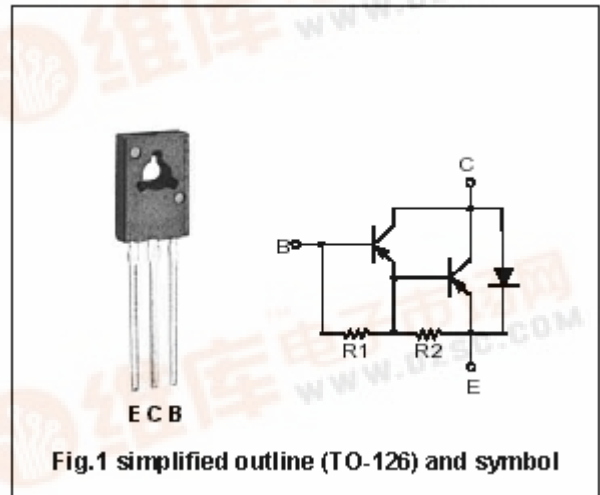
- With TO-126 package
- Complement to type BD675A/677A/679A/681
- DARLINGTON
- High DC current gain

APPLICATIONS

- For medium power linear and switching applications

PINNING

PIN	DESCRIPTION
1	Emitter
2	Collector;connected to mounting base
3	Base



Absolute maximum ratings (Ta=25)

SYMBOL	PARAMETER	CONDITIONS	VALUE	UNIT
V _{CBO}	Collector-base voltage	BD676A	-45	V
		BD678A	-60	
		BD680A	-80	
		BD682	-100	
V _{CEO}	Collector-emitter voltage	BD676A	-45	V
		BD678A	-60	
		BD680A	-80	
		BD682	-100	
V _{EBO}	Emitter -base voltage	Open collector	-5	V
I _C	Collector current		-4	A
I _{CM}	Collector current-Peak		-6	A
I _B	Base current		-0.1	A
P _C	Collector power dissipation	T _C =25	40	W
T _j	Junction temperature		150	
T _{stg}	Storage temperature		-65~150	

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CHARACTERISTICS

T_j=25 unless otherwise specified

SYMBOL	PARAMETER		CONDITIONS	MIN	TYP.	MAX	UNIT
V _{(BR)CEO}	Collector-emitter breakdown voltage	BD676A	I _C =-50mA; I _B =0	-45			V
		BD678A		-60			
		BD680A		-80			
		BD682		-100			
V _{CEsat}	Collector-emitter saturation voltage	BD676A/678A/680A	I _C =-2A; I _B =-40mA			-2.8	V
		BD682	I _C =-1.5A; I _B =-30mA			-2.5	
V _{BE(on)}	Emitter-base voltage	BD676A/678A/680A	I _C =-2A; V _{CE} =-3V			-2.5	V
		BD682	I _C =-1.5A; V _{CE} =-3V				
I _{CBO}	Collector cut-off current		V _{CB} =rated BV _{CEO} ; I _E =0 T _a =100			-0.2 -2.0	mA
I _{CEO}	Collector cut-off current		V _{CE} =1/2rated BV _{CEO} ; I _B =0			-0.5	mA
I _{EBO}	Emitter cut-off current		V _{EB} =-5V; I _C =0			-2.0	mA
h _{FE}	DC current gain	BD676A/678A/680A	I _C =-2A; V _{CE} =-3V	750			
		BD682	I _C =-1.5A; V _{CE} =-3V	750			

PACKAGE OUTLINE

